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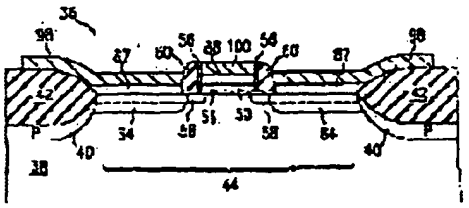
(54) TRANSISTOR AND MANUFACTURING METHOD THEREFOR

(57)Abstract:
PURPOSE: To eliminate complexity of a manufacturing process for an elevated sourcedrain composition insulated gate FET and limitation of a device performance and easily to realize a low electric resistance mutual junction.
CONSTITUTION: A transistor construction 36 is efficiently distributed near a shallow intensive dope source-drain junction region 64 and a gate conductor-gate boundary 51 and an even dope lower gate region 50 with a high concentration is generated. Terminals of a gate, a source and a drain of the transistor construction 36 are mutually junctioned with other devices in the neighborhood and the distance via the use of reaction high fusion metal mutual junctions 98 and 100. An elevated source-drain type including an elevated source-drain junction region 87 which is simultaneously manufactured with a first upper side gate conductor region 88 can be optionally comprised.



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